

isc N-Channel MOSFET Transistor

2SK4161D

FEATURES

- Drain Current –I_D=100A@ T_C=25 °C
- Drain Source Voltage-
 - : V_{DSS}=60V(Min)
- Static Drain-Source On-Resistance
 - : $R_{DS(on)}$ = 4.8m Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

pin 1.Gate 2.Drain 3.Source TO-3PN package

DESCRIPTION

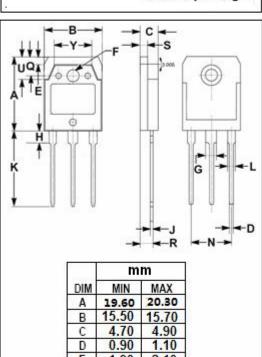
• Designed for use in switch mode power supplies .

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|-------|--------------|
| V _{DSS} | Drain-Source Voltage | 60 | V |
| V _{GS} | Gate-Source Voltage-Continuous | ±20 | V |
| I _D | Drain Current-Continuous | 100 | А |
| I _{DM} | Drain Current-Single Pluse | 200 | А |
| P _D | Total Dissipation @T _C =25°C | 132 | W |
| TJ | Max. Operating Junction Temperature | 175 | $^{\circ}$ |
| T _{stg} | Storage Temperature -55~175 | | $^{\circ}$ C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|--------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance, Junction to Case | 1.13 | °C/W |



| DIM | MIN | MAX |
|-----|-------|-------|
| Α | 19.60 | 20.30 |
| В | 15.50 | 15.70 |
| C | 4.70 | 4.90 |
| D | 0.90 | 1.10 |
| E | 1.90 | 2.10 |
| F | 3.40 | 3.60 |
| G | 2.90 | 3.20 |
| Н | 3.20 | 3.40 |
| J | 0.595 | 0.605 |
| K | 19.80 | 20.70 |
| L | 1.90 | 2.20 |
| N | 10.89 | 10.91 |
| Q | 4.90 | 5.10 |
| R | 3.35 | 3.45 |
| S | 1.995 | 2.100 |
| U | 5.90 | 6.20 |
| Y | 9.90 | 10.10 |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------------|--|---|------|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.1mA | 60 | | V |
| V _{GS(th)} | Gate Threshold Voltage V _{DS} = V _{GS} ; I _D =1mA | | 3.25 | 3.95 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 35A | | 4.8 | mΩ |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±15V;V _{DS} = 0 | | ±10 | uA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =40V; V _{GS} = 0 | | 100 | μА |
| V _{SD} | Forward On-Voltage | I _S =50A; V _{GS} = 0 | | 1.2 | V |



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